

MATERIALS SCIENCE & ENGINEERING

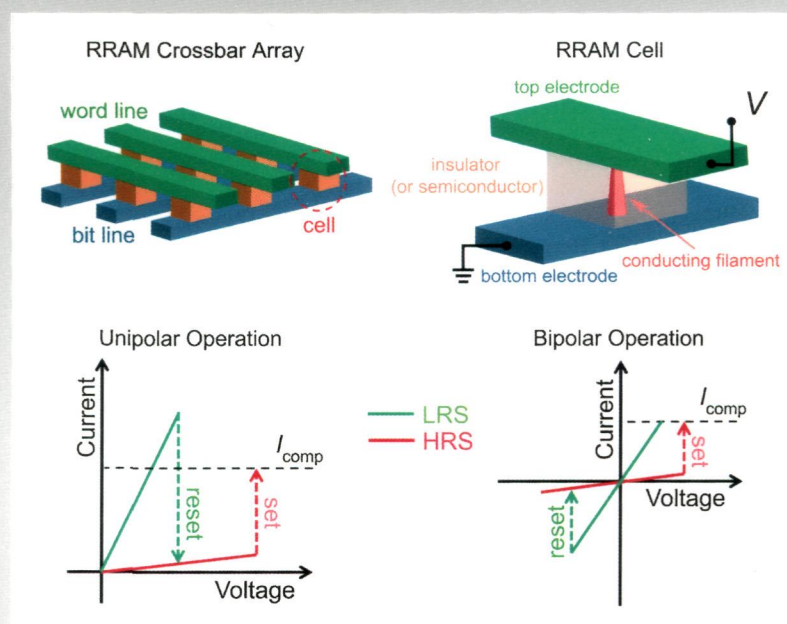
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Recent progress in resistive random access memories:
Materials, switching mechanisms, and performance

F. Pan, S. Gao, C. Chen, C. Song, F. Zeng



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